

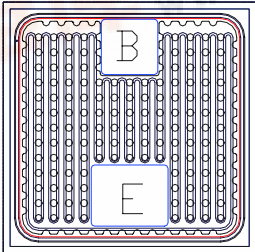
A1013 Silicon PNP Epitaxial Transistor

Description :The A1013 is designed for color TV class B sound output applications

Features: ●High voltage: $V_{CEO}=160V$

●Complementary to C2383

Chip Appearance

	Chip Size		1100um × 1100um
	Chip Thickness		210 ± 20um
	Bonding Pad Size	Base	240um × 240um
		Emitter	330um × 260um
	Front Metal		Al
	Backside Metal		Au
	Scribe line width		60um
	Wafer Size		6 inch

Electrical Characteristics(Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=-150V, I_E=0$		-1.0	uA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-6V, I_C=0$		-1.0	uA
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=-0.1mA$	-160		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=-10mA$	-160		V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=-0.1mA$	-6.0		V
DC Current Gain	h_{FE}	$V_{CE}=-5V, I_C=-200mA$	60	320	
Collector Saturation Voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-50mA$		-1.5	V

